TITLE OF INVENTION: PATTERN FORMING METHOD AND LAMINATE

ABSTRACT

The present invention is a pattern forming method using EUV lithography, the pattern forming method including steps of: forming a resist upper layer film on at least one surface side of a substrate; irradiating the resist upper layer film with EUV light; and developing the resist upper layer film to form a pattern, wherein a multilayer reflective film layer is disposed between the substrate and the resist upper layer film, and the multilayer reflective film layer has a structure in which two or more materials different in refractive index n at a wavelength of the EUV light are alternately laminated. The present invention provides: a pattern forming method and a laminate that can contribute to sensitivity enhancement while maintaining LWR of a resist upper layer film are provided.

[FIG. 1(A)-1(H)]